

introducing an argon ion into a selected portion of said semiconductor film using a first mask covering a first portion of said semiconductor film provided over said semiconductor film;

heating said semiconductor film to getter said crystallization promoting material into said selected portion of said semiconductor film;

forming a second mask over said semiconductor film; and  
etching a part of said first portion of said semiconductor film and said selected portion of said semiconductor film using said second mask after said heating to form an active layer of the semiconductor device.

56. A method for manufacturing a semiconductor device comprising:

forming a semiconductor film comprising silicon over a substrate;

providing said semiconductor film with a crystallization promoting material;

introducing an argon ion into a selected portion of said semiconductor film using a first mask covering a first portion of said semiconductor film provided over said semiconductor film;

heating said semiconductor film to crystallize said semiconductor film using said crystallization promoting material

Attorney's Docket No.: 07977-052001/US3053

and to getter said crystallization promoting material into said selected portion of said semiconductor film;

forming a second mask over said semiconductor film; and

etching a part of said first portion of said semiconductor film and said selected portion of said semiconductor film using said second mask after said heating to form an active layer of the semiconductor device.